







DLP230GP

#### ZHCSI32C - OCTOBER 2018 - REVISED JULY 2023

# DLP230GP 0.23 qHD S246

# 1 特性

- 超紧凑 0.23-Inch (5.95-mm) 对角线微镜阵列
  - 显示器 960 × 540 像素阵列
  - 5.4µm 微镜间距
  - 17°微镜倾斜(相对于平坦表面)
  - 采用侧面照明,实现最优的效率和光学引擎尺寸
  - 偏振无关型铝微镜表面
- 8 位 SubLVDS 输入数据总线
- 适用于显示和照明控制应用的专用 DLPC3432 and DLPC3472 控制器选项
- 专用 DLPA2000, DLPA2005 or DLPA3000 PMIC/LED 驱动器,确保可靠运行

# 2 应用

- 显示:
  - 超高移动性、超低功耗 Pico 投影仪
  - 手机、平板电脑和笔记本电脑
  - 智能扬声器
  - 智能家居

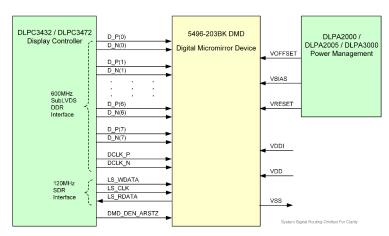
# 3 说明

DLP230GP 数字微镜器件 (DMD) 是一款数控微光 机电系统 (MOEMS) 空间照明调制器 (SLM)。当与 适当的光学系统耦合连接时,DLP230GP DMD 可显 示非常清晰的高质量图像或视频。DLP230GP 是由 DLP230GP DMD 和 DLPC3432 and DLPC3472 控制 器所组成的芯片组的一部分。DLPA2000, DLPA2005 or DLPA3000 PMIC/LED 驱动器也支持此芯片组。 DLP230GP 外形小巧,非常适合注重小尺寸和低功耗 的便携设备。紧凑型 DLP230GP DMD 与控制器和 PMIC/LED 驱动器共同组成完整的系统解决方案,可实 现小巧外形、低功耗以及高画质显示。

#### 器件信息

器件型号 封装(1)		封装尺寸(标称值)			
DLP230GP	FQP (54)	16.8 mm × 5.92 mm × 3.58 mm			

(1) 如需了解所有可用封装,请参阅数据表末尾的可订购产品附



简化版应用



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4 Revision History 注:以前版本的页码可能与当前版本的页码不同

Changes from Revision B (May 2022) to Revision C (July 2023)	Page
Added section "ILLUMINATION" to Recommended Operating Conditions	
• Corrected thermal resistance in Thermal Information from 13 °C/W to 9 °C/W	
Updated Micromirror Array Temperature Calculations	25
Added Micromirror Power Density Calculation	
Changes from Revision A (October 2021) to Revision B (May 2022)	Page
Updated Absolute Maximum Ratings disclosure to the latest TI standard	6
Updated Micromirror Array Optical Characteristics	19
Added Third-Party Products Disclaimer	39
Changes from Revision (October 2018) to Revision A (October 2021)	Page
• 更新了整个文档中的表格、图和交叉参考的编号格式	1
Updated  T <sub>DELTA</sub>   MAX from 25°C to 15°C	7



# **5 Pin Configuration and Functions**

# 图 5-1. FQP Package 54-Pin CLGA Bottom View

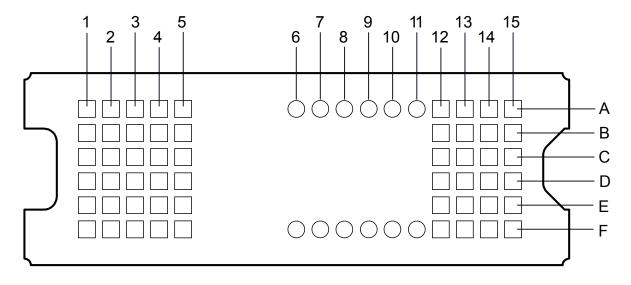


表 5-1. Connector Pins

PIN <sup>(1)</sup>		TYPE	SIGNAL	DATA RATE	DESCRIPTION	PACKAGE NET
NAME	NO.	ITPE	SIGNAL	DAIA RAIE	DESCRIPTION	LENGTH <sup>(2)</sup> (mm)
DATA INPUTS				_		
D_N(0)	A2 I		SubLVDS	Double	Data, negative	1.96
D_N(1)	A1	ı	SubLVDS	Double	Data, negative	1.42
D_N(2)	C1	I	SubLVDS	Double	Data, negative	1.35
D_N(3)	B4	ı	SubLVDS	Double	Data, negative	3.36
D_N(4)	F5	ı	SubLVDS	Double	Data, negative	4.29
D_N(5)	N(5) D4 I SubLVDS Double Data, negative		3.20			
D_N(6)	N(6) E1 I SubLVDS Double Data, negative		Data, negative	1.76		
D_N(7)	F3	I	SubLVDS	Double	Data, negative	2.66
D_P(0)	A3	ı	SubLVDS	Double	Data, positive	1.97
D_P(1)	B1	I	SubLVDS	Double	Data, positive	1.49
D_P(2)	C2	I	SubLVDS	Double	Data, positive	1.44
D_P(3)	A4	I	SubLVDS	Double	Data, positive	3.45
D_P(4)	E5	Ţ	SubLVDS	Double	Data, positive	4.32
D_P(5)	D5	ı	SubLVDS	Double	Data, positive	3.27
D_P(6)	E2	ı	SubLVDS	Double	Data, positive	1.85
D_P(7)	F2	I	SubLVDS	Double	Data, positive	2.75
DCLK_N	C3	I	SubLVDS	Double	Clock, negative	1.94
DCLK_P	D3	I	SubLVDS	Double	Clock, positive	2.02
CONTROL INPUTS				•		
LS_WDATA	A12	I	LPSDR <sup>(1)</sup>	Single	Write data for low speed interface.	2.16
LS_CLK	B12	I	LPSDR	Single	Clock for low-speed interface.	3.38
DMD_DEN_ARSTZ	B14	I	LPSDR	Single	Asynchronous reset DMD signal. A low	0.67
DMD_DEN_ARSTZ	F1	I	LPSDR	Single	signal places the DMD in reset. A high signal releases the DMD from reset and places it in active mode.	14.90



# 表 5-1. Connector Pins (continued)

PIN <sup>(1)</sup>		3 3-1. Connector			PACKAGE NET
NO.	TYPE	SIGNAL D	ATA RATE	DESCRIPTION	LENGTH <sup>(2)</sup> (mm)
C13	0	LPSDR Sin	ıgle	Read data for low-speed interface.	2.44
<u> </u>					
A15	Power			Supply voltage for positive bias level at	
A5	Power			micromirrors.	
F13	Power			Supply voltage for HVCMOS core	
F4	Power			logic. Supply voltage for stepped high level at micromirror address electrodes.  Supply voltage for offset level at micromirrors.	
B15	Power			Supply voltage for negative reset level	
B5	Power			at micromirrors.	
C15	Power				
C5	Power				
D14	Power			Supply voltage for LVCMOS core logic	
D15	Power			Supply voltage for LPSDR inputs. Supply voltage for normal high level at micromirror address electrodes.	
E14	Power				
E15	Power				
F14	Power				
F15	Power				
C14	Power				
C4	Power			Supply voltage for Subl VDS receivers	
D13	Power			Supply voltage for SubLyb3 receivers.	
E13	Power				
A13	Ground				
A14	Ground				
B13	Ground				
B2	Ground				
B3	Ground				
C12	Ground				
D1	Ground				
D12	Ground			]	
D2	Ground				
E12	Ground				
E3	Ground				
E4	Ground			]	
F12	Ground				
	C13  A15  A5  F13  F4  B15  B5  C15  C5  D14  D15  E14  E15  F14  C4  D13  E13  A13  A14  B13  B2  B3  C12  D1  D12  D2  E12  E3  E4	NO.           C13         O           A15         Power           F13         Power           F13         Power           F4         Power           B5         Power           C15         Power           D14         Power           D15         Power           E14         Power           F15         Power           C14         Power           C14         Power           C13         Power           C14         Power           C15         Power           E16         Power           E17         Power           C14         Power           C15         Power           C16         Power           C17         Power           C18         Power           C19         Power           C10         Power           C11         Power           C12         Ground           B13         Ground           C12         Ground           D1         Ground           D12         Ground           E12         Ground	NO.   C13   O   LPSDR   Sin	NO.   C13	NO. TYPE SIGNAL DATA RATE DESCRIPTION  C13 O LPSDR Single Read data for low-speed interface.  A15 Power Supply voltage for positive bias level at micromirrors.  F13 Power Supply voltage for HVCMOS core logic. Supply voltage for stepped high level at micromirror address electrodes. Supply voltage for negative reset level at micromirrors.  B15 Power Supply voltage for negative reset level at micromirrors.  C15 Power Supply voltage for negative reset level at micromirrors.  C15 Power Supply voltage for negative reset level at micromirrors.  Supply voltage for LVCMOS core logic. Supply voltage for LPSDR inputs. Supply voltage for normal high level at micromirror address electrodes.  E14 Power Supply voltage for normal high level at micromirror address electrodes.  E15 Power Supply voltage for SubLVDS receivers.  E14 Power Supply voltage for SubLVDS receivers.  E15 Power Supply voltage for SubLVDS receivers.  C14 Power Supply voltage for SubLVDS receivers.  C15 Power Supply voltage for SubLVDS receivers.  C16 Power Supply voltage for SubLVDS receivers.  C17 Power Supply voltage for SubLVDS receivers.  C18 Power Supply voltage for SubLVDS receivers.  C2 Power Supply voltage for SubLVDS receivers.  C3 Ground Supply voltage for SubLVDS receivers.  C4 Power Supply voltage for SubLVDS receivers.  C5 Power Supply voltage for SubLVDS receivers.  C6 Power Supply voltage for SubLVDS receivers.  C7 Common return.  C8 Ground Supply voltage for SubLVDS receivers.

- (1) Low speed interface is LPSDR and adheres to the Electrical Characteristics and AC/DC Operating Conditions table in JEDEC Standard No. 209B, Low Power Double Data Rate (LPDDR). See JESD209B.
- (2) Net trace lengths inside the package:

Relative dielectric constant for the FQP ceramic package is 9.8.

Propagation speed = 11.8 / sqrt (9.8) = 3.769 in/ns.

Propagation delay = 0.265 ns/inch = 265 ps/in = 10.43 ps/mm.

(3) The following power supplies are all required to operate the DMD: V<sub>DD</sub>, V<sub>DDI</sub>, V<sub>OFFSET</sub>, V<sub>BIAS</sub>, V<sub>RESET</sub>. All V<sub>SS</sub> connections are also required.



# 表 5-2. Test Pads

NUMBER	SYSTEM BOARD
A6	Do not connect
A7	Do not connect
A8	Do not connect
A9 Do not connect	
A10	Do not connect
A11	Do not connect
F6	Do not connect
F7	Do not connect
F8	Do not connect
F9	Do not connect
F10 Do not connect	
F11	Do not connect



# 6 Specifications

# 6.1 Absolute Maximum Ratings

see (1)

			MIN	MAX	UNIT
	V <sub>DD</sub>	Supply voltage for LVCMOS core logic <sup>(2)</sup> Supply voltage for LPSDR low speed interface	-0.5	2.3	V
	V <sub>DDI</sub>	Supply voltage for SubLVDS receivers <sup>(2)</sup>	-0.5	2.3	V
	V <sub>OFFSET</sub>	Supply voltage for HVCMOS and micromirror electrode <sup>(2)</sup> (3)	-0.5	11	V
Supply voltage	V <sub>BIAS</sub>	Supply voltage for micromirror electrode <sup>(2)</sup>	-0.5	19	V
	V <sub>RESET</sub>	Supply voltage for micromirror electrode <sup>(2)</sup>	-15	0.5	V
	V <sub>DDI</sub> -V <sub>DD</sub>	Supply voltage delta (absolute value) <sup>(4)</sup>		0.3	V
	V <sub>BIAS</sub> -V <sub>OFFSET</sub>	Supply voltage delta (absolute value) <sup>(5)</sup>		11	V
	V <sub>BIAS</sub> -V <sub>RESET</sub>	Supply voltage delta (absolute value) <sup>(6)</sup>		34	V
Input voltage	Input voltage for other inp	outs LPSDR <sup>(2)</sup>	-0.5	V <sub>DD</sub> + 0.5	V
	Input voltage for other inputs SubLVDS <sup>(2) (7)</sup>			V <sub>DDI</sub> + 0.5	V
Input pine	V <sub>ID</sub>	SubLVDS input differential voltage (absolute value) <sup>(7)</sup>		810	mV
Supply voltage  VBIAS VRES   VDDI  VBIA:  VBIA:  INput	I <sub>ID</sub>	SubLVDS input differential current		10	mA
Clock	$f_{ m clock}$	Clock frequency for low speed interface LS_CLK		130	MHz
frequency	$f_{clock}$	Clock frequency for high speed interface DCLK		620	MHz
	T <sub>ARRAY</sub> and T <sub>WINDOW</sub>	Temperature – operational <sup>(8)</sup>	-20	90	°C
Environmental	TARRAY ATIU TWINDOW	Temperature – non-operational <sup>(8)</sup>	-40	90	°C
	T <sub>DELTA</sub>	Absolute temperature delta between any point on the window edge and the ceramic test point TP1 <sup>(9)</sup>		30	°C
	T <sub>DP</sub>	Dew Point - operating and non-operating		81	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) All voltage values are with respect to the ground terminals (V<sub>SS</sub>). The following power supplies are all required to operate the DMD: V<sub>DD</sub>, V<sub>DDI</sub>, V<sub>OFFSET</sub>, V<sub>BIAS</sub>, and V<sub>RESET</sub>. All V<sub>SS</sub> connections are also required.
- (3) V<sub>OFFSET</sub> supply transients must fall within specified voltages.
- (4) Exceeding the recommended allowable absolute voltage difference between V<sub>DDI</sub> and V<sub>DD</sub> may result in excessive current draw.
- (5) Exceeding the recommended allowable absolute voltage difference between V<sub>BIAS</sub> and V<sub>OFFSET</sub> may result in excessive current draw.
- 6) Exceeding the recommended allowable absolute voltage difference between V<sub>BIAS</sub> and V<sub>RESET</sub> may result in excessive current draw.
- (7) This maximum input voltage rating applies when each input of a differential pair is at the same voltage potential. Sub-LVDS differential inputs must not exceed the specified limit or damage may result to the internal termination resistors.
- (8) The highest temperature of the active array (as calculated by the #7.6) or of any point along the window edge is defined in 图 7-1. The location of thermal test point TP2 in 图 7-1 is intended to measure the highest window edge temperature. If a particular application causes another point on the window edge to be at a higher temperature, that point should be used.
- (9) Temperature delta is the highest difference between the ceramic test point 1 (TP1) and anywhere on the window edge as shown in 🛭 7-1. The window test point TP2 shown in 🖺 7-1 is intended to result in the worst case delta. If a particular application causes another point on the window edge to result in a larger delta temperature, that point should be used.

# **6.2 Storage Conditions**

Applicable for the DMD as a component or non-operating in a system.

		MIN	MAX	UNIT
T <sub>DMD</sub>	DMD storage temperature	-40	85	°C
T <sub>DP</sub>	Average dew point temperature (non-condensing) (1)		24	°C
T <sub>DP-ELR</sub>	Elevated dew point temperature range (non-condensing) (2)	28	36	°C
CT <sub>ELR</sub>	Cumulative time in elevated dew point temperature range		6	months

(1) The average over time (including storage and operating) that the device is not in the elevated dew point temperature range.



(2) Exposure to dew point temperatures in the elevated range during storage and operation should be limited to less than a total cumulative time of CT<sub>ELR</sub>.

# 6.3 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	±2000	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

# **6.4 Recommended Operating Conditions**

Over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup> (2)

		MIN	NOM	MAX	UNIT
SUPPLY VOLTAG	SE RANGE <sup>(3)</sup>				
$V_{DD}$	Supply voltage for LVCMOS core logic Supply voltage for LPSDR low-speed interface	1.65	1.8	1.95	V
V <sub>DDI</sub>	Supply voltage for SubLVDS receivers	1.65	1.8	1.95	V
V <sub>OFFSET</sub>	Supply voltage for HVCMOS and micromirror electrode <sup>(4)</sup>	9.5	10	10.5	V
V <sub>BIAS</sub>	Supply voltage for mirror electrode	17.5	18	18.5	V
V <sub>RESET</sub>	Supply voltage for micromirror electrode	-14.5	-14	-13.5	V
V <sub>DDI</sub> -V <sub>DD</sub>	Supply voltage delta (absolute value) <sup>(5)</sup>			0.3	V
V <sub>BIAS</sub> -V <sub>OFFSET</sub>	Supply voltage delta (absolute value) <sup>(6)</sup>			10.5	V
V <sub>BIAS</sub> -V <sub>RESET</sub>	Supply voltage delta (absolute value) <sup>(7)</sup>			33	V
CLOCK FREQUE	NCY				
$f_{ m clock}$	Clock frequency for low speed interface LS_CLK <sup>(8)</sup>	108		120	MHz
$f_{ m clock}$	Clock frequency for high speed interface DCLK <sup>(9)</sup>	300		540	MHz
	Duty cycle distortion DCLK	44%		56%	
SUBLVDS INTER	FACE <sup>(9)</sup>	'			
V <sub>ID</sub>	SubLVDS input differential voltage (absolute value). See 图 6-8, 图 6-9	150	250	350	mV
V <sub>CM</sub>	Common mode voltage. See 图 6-8, 图 6-9	700	900	1100	mV
V <sub>SUBLVDS</sub>	SubLVDS voltage. See 图 6-8, 图 6-9	575		1225	mV
Z <sub>LINE</sub>	Line differential impedance (PWB/trace)	90	100	110	Ω
Z <sub>IN</sub>	Internal differential termination resistance. See 图 6-10	80	100	120	Ω
	100-Ω differential PCB trace	6.35		152.4	mm



# 6.4 Recommended Operating Conditions (continued)

Over operating free-air temperature range (unless otherwise noted)(1) (2)

		MIN	NOM	MAX	UNIT
ENVIRONME	NTAL				
T <sub>ARRAY</sub>	Array Temperature – long-term operational <sup>(10)</sup> (11) (12) (13)	0		40 to 70 <sup>(12)</sup>	°C
	Array Temperature – short-term operational, 25 hr max <sup>(11)</sup> (14)	-20		-10	°C
	Array Temperature – short-term operational, 500 hr max <sup>(11)</sup> (14)	-10		0	°C
	Array Temperature – short-term operational, 500 hr max <sup>(11)</sup> (14)	70		75	°C
T <sub>WINDOW</sub>	Window Temperature – operational <sup>(15)</sup> (16)			90	°C
T <sub>DELTA</sub>	Absolute temperature delta between any point on the window edge and the ceramic test point TP1 <sup>(17)</sup>			15	°C
T <sub>DP-AVG</sub>	Average dew point temperature (non-condensing) (18)			24	°C
T <sub>DP-ELR</sub>	Elevated dew point temperature range (non-condensing) (19)	28		36	°C
CT <sub>ELR</sub>	Cumulative time in elevated dew point temperature range			6	months
ILLUMINATIO	N .				
ILL <sub>UV</sub>	Illumination power at wavelengths < 410 nm <sup>(10)</sup>			10	mW/cm <sup>2</sup>
ILL <sub>VIS</sub>	Illumination power at wavelengths ≥ 410 nm and ≤ 800 nm <sup>(20)</sup>			26.1	W/cm <sup>2</sup>
ILL <sub>IR</sub>	Illumination power at wavelengths > 800 nm			10	mW/cm <sup>2</sup>
ILL <sub>BLU</sub>	Illumination power at wavelengths ≥ 410 nm and ≤ 475 nm <sup>(20)</sup>			8.3	W/cm <sup>2</sup>
ILL <sub>BLU1</sub>	Illumination power at wavelengths ≥ 410 nm and ≤ 445 nm <sup>(20)</sup>			1.5	W/cm <sup>2</sup>
$ILL_{\theta}$	Illumination marginal ray angle <sup>(15)</sup>			55	deg

- The functional performance of the device specified in this data sheet is achieved when operating the device within the limits defined by the #6.4 No level of performance is implied when operating the device above or below the #6.4 limits.
- The following power supplies are all required to operate the DMD: VDD, VDDI, VOFFSET, VBIAS, and VRESET. All VSS connections are also (2) required.
- All voltage values are with respect to the ground pins (V<sub>SS</sub>). (3)
- (4) V<sub>OFFSET</sub> supply transients must fall within specified max voltages.
- To prevent excess current, the supply voltage delta  $|V_{DDI} V_{DD}|$  must be less than the specified limit. (5)
- To prevent excess current, the supply voltage delta  $|V_{BIAS} V_{OFFSET}|$  must be less than the specified limit. (6)
- (7) To prevent excess current, the supply voltage delta |V<sub>BIAS</sub> - V<sub>RESET</sub>| must be less than the specified limit.
- LS\_CLK must run as specified to ensure internal DMD timing for reset waveform commands. (8)
- Refer to the SubLVDS timing requirements in # 6.7.
- (10) Simultaneous exposure of the DMD to the maximum Recommended Operating Conditions for temperature and UV illumination will reduce device lifetime.
- (11) The array temperature cannot be measured directly and must be computed analytically from the temperature measured at test point 1 (TP1) shown in 图 7-1 and the package thermal resistance using #7.6.
- (12) Per 🛚 6-1, the maximum operational array temperature should be derated based on the micromirror landed duty cycle that the DMD experiences in the end application. Refer to #7.8 for a definition of micromirror landed duty cycle.
- (13) Long-term is defined as the usable life of the device.
- (14) Short-term is the total cumulative time over the useful life of the device.
   (15) The maximum marginal ray angle of the incoming illumination light at any point in the micromirror array, including at the pond of micromirrors (POM), should not exceed 55 degrees from the normal to the device array plane. The device window aperture has not necessarily been designed to allow incoming light at higher maximum angles to pass to the micromirrors, and the device performance has not been tested nor qualified at angles exceeding this. Illumination light exceeding this angle outside the micromirror array (including POM) will contribute to thermal limitations described in this document and may negatively affect lifetime.
- (16) Window temperature is the highest temperature on the window edge shown in ₹ 7-1. The location of thermal test point TP2 in ₹ 7-1 is intended to measure the highest window edge temperature. If a particular application causes another point on the window edge to be at a higher temperature, that point should be used.
- (17) Temperature delta is the highest difference between the ceramic test point 1 (TP1) and anywhere on the window edge shown in 🛭 7-1. The window test point TP2 shown in 🛭 7-1 is intended to result in the worst-case delta temperature. If a particular application causes another point on the window edge to result in a larger delta temperature, that point should be used.
- (18) The average over time (including storage and operating) that the device is not in the 'elevated dew point temperature range'.
- (19) Exposure to dew point temperatures in the elevated range during storage and operation should be limited to less than a total cumulative time of CT<sub>ELR</sub>.
- (20) The maximum allowable optical power incident on the DMD is limited by the maximum optical power density for each wavelength range specified and the micromirror array temperature (T<sub>ARRAY</sub>).

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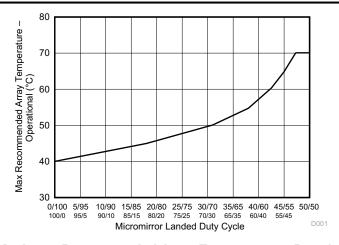


图 6-1. Maximum Recommended Array Temperature – Derating Curve



#### **6.5 Thermal Information**

		DLP230GP	
	THERMAL METRIC(1)	FQP (CLGA)	UNIT
		54 PINS	
Thermal resistance	Active area to test point 1 (TP1) <sup>(1)</sup>	9.0	°C/W

(1) The DMD is designed to conduct absorbed and dissipated heat to the back of the package. The cooling system must be capable of maintaining the package within the temperature range specified in the #6.4. The total heat load on the DMD is largely driven by the incident light absorbed by the active area, although other contributions include light energy absorbed by the window aperture and electrical power dissipated by the array. Optical systems should be designed to minimize the light energy falling outside the window clear aperture since any additional thermal load in this area can significantly degrade the reliability of the device.

# 6.6 Electrical Characteristics

Over operating free-air temperature range (unless otherwise noted)(1)

	PARAMETER	TEST CONDITIONS(2)	MIN	TYP MAX	UNIT	
CURREN	Г		<b>'</b>			
	C	V <sub>DD</sub> = 1.95 V			Л	
I <sub>DD</sub>	Supply current: V <sub>DD</sub> <sup>(3) (4)</sup>	V <sub>DD</sub> = 1.8 V			mA	
	(3) (4)	V <sub>DDI</sub> = 1.95 V			A	
I <sub>DDI</sub>	Supply current: V <sub>DDI</sub> <sup>(3) (4)</sup>	V <sub>DDI</sub> = 1.8 V			mA	
	(5) (6)	V <sub>OFFSET</sub> = 10.5 V			^	
I <sub>OFFSET</sub>	Supply current: V <sub>OFFSET</sub> (5) (6)	V <sub>OFFSET</sub> = 10 V			mA	
1	Supply current: V (5) (6)	V <sub>BIAS</sub> = 18.5 V			m A	
I <sub>BIAS</sub>	Supply current: V <sub>BIAS</sub> <sup>(5)</sup> <sup>(6)</sup>	V <sub>BIAS</sub> = 18 V			mA	
	Supply current: V (6)	V <sub>RESET</sub> = -14.5 V			m A	
I <sub>RESET</sub>	Supply current: V <sub>RESET</sub> (6)	V <sub>RESET</sub> = -14 V			mA	
POWER <sup>(7</sup>			•			
n	Supply power dissipation: V (3) (4)	V <sub>DD</sub> = 1.95 V			1,,,	
$P_{DD}$	Supply power dissipation: V <sub>DD</sub> <sup>(3)</sup> <sup>(4)</sup>	V <sub>DD</sub> = 1.8 V			mW	
D	Supply power dissipation: V (3) (4)	V <sub>DDI</sub> = 1.95 V			m\\/	
$P_{DDI}$	Supply power dissipation: V <sub>DDI</sub> <sup>(3)</sup> <sup>(4)</sup>	V <sub>DD</sub> = 1.8 V			mW	
П	Supply power dissipation: V <sub>OFFSET</sub> (5)	V <sub>OFFSET</sub> = 10.5 V			m\\/	
P <sub>OFFSET</sub>	(6)	V <sub>OFFSET</sub> = 10 V			mW	
n	Supply power dissipation: V (5) (6)	V <sub>BIAS</sub> = 18.5 V			m\\/	
P <sub>BIAS</sub>	Supply power dissipation: V <sub>BIAS</sub> <sup>(5)</sup> (6)	V <sub>BIAS</sub> = 18 V			mW	
D	Complement distinction (6)	V <sub>RESET</sub> = -14.5 V			\^/	
P <sub>RESET</sub>	Supply power dissipation: V <sub>RESET</sub> (6)	V <sub>RESET</sub> = -14 V			mW	
P <sub>TOTAL</sub>	Supply power dissipation: Total				mW	
LPSDR IN	PUT <sup>(8)</sup>					
V <sub>IH(DC)</sub>	DC input high voltage <sup>(9)</sup>		0.7 × V <sub>DD</sub>	V <sub>DD</sub> + 0.3	V	
V <sub>IL(DC)</sub>	DC input low voltage <sup>(9)</sup>		-0.3	0.3 × V <sub>DD</sub>	V	
V <sub>IH(AC)</sub>	AC input high voltage <sup>(9)</sup>		0.8 × V <sub>DD</sub>	V <sub>DD</sub> + 0.3	V	
V <sub>IL(AC)</sub>	AC input low voltage <sup>(9)</sup>		-0.3	0.2 × V <sub>DD</sub>	V	
$\Delta V_{T}$	Hysteresis ( V <sub>T+</sub> – V <sub>T-</sub> )	图 6-10	0.1 × V <sub>DD</sub>	0.4 × V <sub>DD</sub>	V	
I <sub>IL</sub>	Low-level input current	V <sub>DD</sub> = 1.95 V; V <sub>I</sub> = 0 V	-100		nA	
I <sub>IH</sub>	High-level input current	V <sub>DD</sub> = 1.95 V; V <sub>I</sub> = 1.95 V		100	nA	
LPSDR O	UTPUT <sup>(10)</sup>		•			
V <sub>OH</sub>	DC output high voltage	I <sub>OH</sub> = -2 mA	0.8 × V <sub>DD</sub>		V	



### **6.6 Electrical Characteristics (continued)**

Over operating free-air temperature range (unless otherwise noted)(1)

	PARAMETER	TEST CONDITIONS(2)	MIN	TYP	MAX	UNIT
V <sub>OL</sub>	DC output low voltage	I <sub>OL</sub> = 2 mA			0.2 × V <sub>DD</sub>	V
CAPACITA	ANCE					
C	Input capacitance LPSDR	f = 1 MHz			10	pF
C <sub>IN</sub>	Input capacitance SubLVDS	f = 1 MHz				pF
C <sub>OUT</sub>	Output capacitance	f = 1 MHz			10	pF
C <sub>RESET</sub>	Reset group capacitance	f = 1 MHz; micromirrors)	90			pF

- (1) Device electrical characteristics are over #6.4 unless otherwise noted.
- (2) All voltage values are with respect to the ground pins (V<sub>SS</sub>).
- (3) To prevent excess current, the supply voltage delta |V<sub>DDI</sub> V<sub>DD</sub>| must be less than the specified limit.
- (4) Supply power dissipation based on non–compressed commands and data.
- (5) To prevent excess current, the supply voltage delta |V<sub>BIAS</sub> V<sub>OFFSET</sub>| must be less than the specified limit.
- (6) Supply power dissipation based on 3 global resets in 300 μs.
- (7) The following power supplies are all required to operate the DMD: V<sub>DD</sub>, V<sub>DDI</sub>, V<sub>OFFSET</sub>, V<sub>BIAS</sub>, V<sub>RESET</sub>. All V<sub>SS</sub> connections are also required.
- (8) LPSDR specifications are for pins LS\_CLK and LS\_WDATA.
- (9) Low-speed interface is LPSDR and adheres to the Electrical Characteristics and AC/DC Operating Conditions table in JEDEC Standard No. 209B, Low-Power Double Data Rate (LPDDR) JESD209B.
- (10) LPSDR specification is for pin LS\_RDATA.

# 6.7 Timing Requirements

Device electrical characteristics are over Recommended Operating Conditions unless otherwise noted.

			MIN	NOM M	AX	UNIT
LPSDR					•	
t <sub>r</sub>	Rise slew rate <sup>(1)</sup>	(30% to 80%) × V <sub>DD</sub> , 图 6-3	1		3	V/ns
$t_f$	Fall slew rate <sup>(1)</sup>	(70% to 20%) × V <sub>DD</sub> , 图 6-3	1		3	V/ns
t <sub>r</sub>	Rise slew rate <sup>(2)</sup>	(20% to 80%) × V <sub>DD</sub> , 图 6-3	0.25			V/ns
$t_f$	Fall slew rate <sup>(2)</sup>	(80% to 20%) × V <sub>DD</sub> , 图 6-3	0.25			V/ns
t <sub>c</sub>	Cycle time LS_CLK	图 6-2	7.7	8.3		ns
t <sub>W(H)</sub>	Pulse duration LS_CLK high	50% to 50% reference points, 图 6-2	3.1			ns
t <sub>W(L)</sub>	Pulse duration LS_CLK low	50% to 50% reference points, 图 6-2	3.1			ns
t <sub>su</sub>	Setup time	LS_WDATA valid before LS_CLK ↑, 图 6-2	1.5			ns
t <sub>h</sub>	Hold time	LS_WDATA valid after LS_CLK ↑, 图 6-2	1.5			ns
t <sub>WINDOW</sub>	Window time <sup>(1)</sup> (3)	Setup time + hold time, 图 6-2	3			ns
t <sub>DERATING</sub>	Window time derating <sup>(1) (3)</sup>	For each 0.25 V/ns reduction in slew rate below 1 V/ns, 图 6-5		0.35		ns
SubLVDS						
t <sub>r</sub>	Rise slew rate	20% to 80% reference points, 图 6-4	0.7	1		V/ns
$t_f$	Fall slew rate	80% to 20% reference points, 图 6-4	0.7	1		V/ns
t <sub>c</sub>	Cycle time DCLK	图 6-6	1.79	1.85		ns
t <sub>W(H)</sub>	Pulse duration DCLK high	50% to 50% reference points, 图 6-6	0.79			ns
t <sub>W(L)</sub>	Pulse duration DCLK low	50% to 50% reference points, 图 6-6	0.79			ns
t <sub>su</sub>	Setup time	D(0:7) valid before DCLK ↑ or DCLK ↓, 图 6-6	Setup and Hol	d times are defir	ed	
t <sub>h</sub>	Hold time	D(0:7) valid after DCLK ↑ or DCLK ↓, 图 6-6	Setup and Hol	d times are defir	ed	
t <sub>WINDOW</sub>	Window time	Setup time + hold time, 图 6-6, 图 6-7	0.3			ns

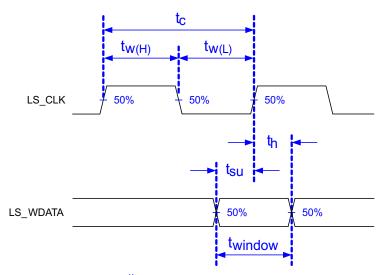


### 6.7 Timing Requirements (continued)

Device electrical characteristics are over *Recommended Operating Conditions* unless otherwise noted.

		MIN	NOM	MAX	UNIT
t <sub>LVDS-</sub> ENABLE+REFGEN	Power-up receiver <sup>(4)</sup>			2000	ns

- (1) Specification is for LS\_CLK and LS\_WDATA pins. Refer to LPSDR input rise slew rate and fall slew rate in 🛭 6-3.
- (2) Specification is for DMD\_DEN\_ARSTZ pin. Refer to LPSDR input rise and fall slew rate in 🛭 6-3.
- (3) Window time derating example: 0.5-V/ns slew rate increases the window time by 0.7 ns, from 3 to 3.7 ns.
- (4) Specification is for SubLVDS receiver time only and does not take into account commanding and latency after commanding.



Low-speed interface is LPSDR and adheres to the # 6.6 and AC/DC Operating Conditions table in JEDEC Standard No. 209B, Low Power Double Data Rate (LPDDR) JESD209B.

### 图 6-2. LPSDR Switching Parameters

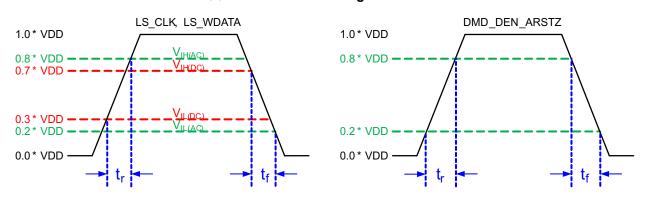


图 6-3. LPSDR Input Rise and Fall Slew Rate

Not to Scale

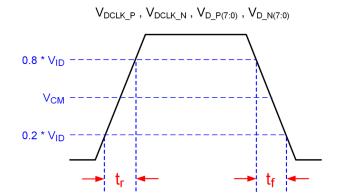
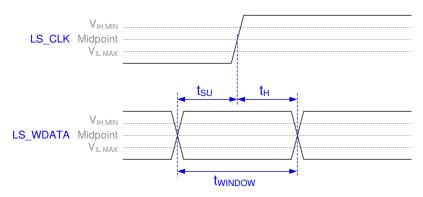


图 6-4. SubLVDS Input Rise and Fall Slew Rate



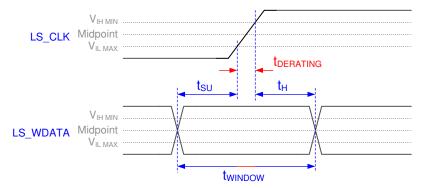


图 6-5. Window Time Derating Concept



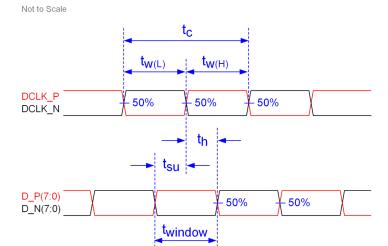
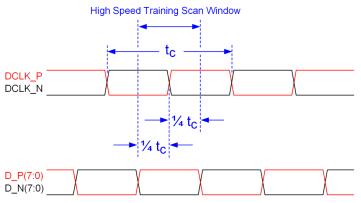


图 6-6. SubLVDS Switching Parameters



Note: Refer to #7.3.3 for details.

图 6-7. High-Speed Training Scan Window

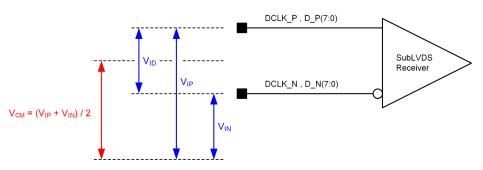
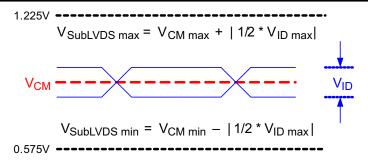


图 6-8. SubLVDS Voltage Parameters

English Data Sheet: DLPS114





#### 图 6-9. SubLVDS Waveform Parameters

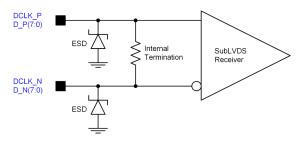


图 6-10. SubLVDS Equivalent Input Circuit

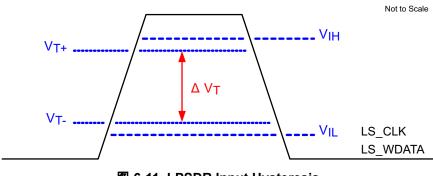


图 6-11. LPSDR Input Hysteresis

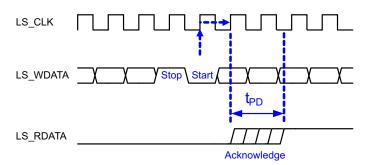
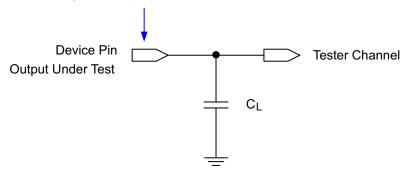


图 6-12. LPSDR Read Out



# Data Sheet Timing Reference Point



See # 7.3.4 for more information.

图 6-13. Test Load Circuit for Output Propagation Measurement

# **6.8 Switching Characteristics**

Over operating free-air temperature range (unless otherwise noted). (1)

	PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
t <sub>PD</sub>	Output propagation, clock to Q, rising edge of LS_CLK input to LS_RDATA output. See 图 6-12.	C <sub>L</sub> = 45 pF		15	ns
	Slew rate, LS_RDATA		0.5	,	V/ns
	Output duty cycle distortion, LS_RDATA		40%	60%	

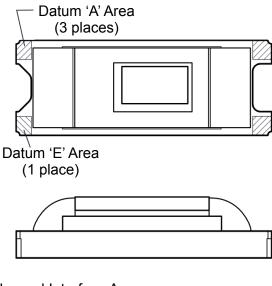
(1) Device electrical characteristics are over # 6.4 unless otherwise noted.



# 6.9 System Mounting Interface Loads

PARAMETER	MIN	NOM	MAX	UNIT
Maximum system mounting interface load to be applied to the:				
Thermal interface area <sup>(1)</sup>			45	N
Clamping and electrical interface area <sup>(1)</sup>			100	N

(1) Uniformly distributed within area shown in ₹ 6-14.



Thermal Interface Area

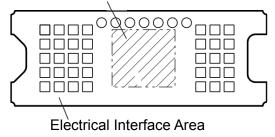


图 6-14. System Interface Loads



# **6.10 Micromirror Array Physical Characteristics**

	PARAMETER		UNIT
Number of active columns	See 图 6-15	960	micromirrors
Number of active rows	See 图 6-15	540	micromirrors
Micromirror (pixel) pitch	See 图 6-16	5.4	μm
Micromirror active array width	Micromirror pitch × number of active columns; see 图 6-15	5.184	mm
Micromirror active array height	Micromirror pitch × number of active rows; see 图 6-15	2.916	mm
Micromirror active border	Pond of micromirror (POM) <sup>(1)</sup>	20	micromirrors/side

(1) The structure and qualities of the border around the active array include a band of partially functional micromirrors called the POM.

These micromirrors are structurally or electrically prevented from tilting toward the bright or ON state, but still require an electrical bias to tilt toward OFF.

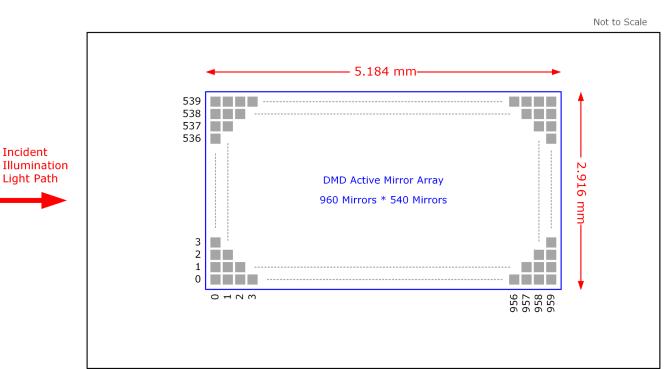


图 6-15. Micromirror Array Physical Characteristics

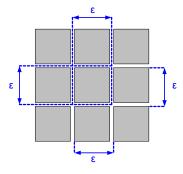


图 6-16. Mirror (Pixel) Pitch



### 6.11 Micromirror Array Optical Characteristics

	PARAMETER	TEST CONDITIONS	MIN	NOM	MAX	UNIT
Micromirror tilt angle		DMD landed state <sup>(1)</sup>		17		degree
Micromirror tilt	angle tolerance <sup>(2) (3) (4) (5)</sup>		-1.4		1.4	degree
Micromirror tilt direction (6) (7)		Landed ON state		180		dograe
Wilcromintor tilt	direction	Landed OFF state		270		degree
Micromirror crossover time <sup>(8)</sup>		Typical performance		1	3	
Micromirror switching time <sup>(9)</sup>		Typical performance	10			μs
	Bright pixel(s) in active area (11)	Gray 10 Screen (12)			0	
Image	Bright pixel(s) in the POM (13)	Gray 10 Screen (12)			1	
performance (10)	Dark pixel(s) in the active area (14)	White Screen			4	micromirrors
	Adjacent pixel(s) (15)	Any Screen			0	
	Unstable pixel(s) in active area (16)	Any Screen			0	

- (1) Measured relative to the plane formed by the overall micromirror array.
- (2) Additional variation exists between the micromirror array and the package datums.
- (3) Represents the landed tilt angle variation relative to the nominal landed tilt angle.
- (4) Represents the variation that can occur between any two individual micromirrors, located on the same device or located on different devices.
- (5) For some applications, it is critical to account for the micromirror tilt angle variation in the overall system optical design. With some system optical designs, the micromirror tilt angle variation within a device may result in perceivable non-uniformities in the light field reflected from the micromirror array. With some system optical designs, the micromirror tilt angle variation between devices may result in colorimetry variations, system efficiency variations, or system contrast variations.
- (6) When the micromirror array is landed (not parked), the tilt direction of each individual micromirror is dictated by the binary contents of the CMOS memory cell associated with each individual micromirror. A binary value of 1 results in a micromirror landing in the ON state direction. A binary value of 0 results in a micromirror landing in the OFF state direction. See 8 6-17.
- (7) Micromirror tilt direction is measured as in a typical polar coordinate system: Measuring counter-clockwise from a 0° reference which is aligned with the +X Cartesian axis.
- (8) The time required for a micromirror to nominally transition from one landed state to the opposite landed state.
- (9) The minimum time between successive transitions of a micromirror.
- (10) Conditions of Acceptance: All DMD image quality returns will be evaluated using the following projected image test conditions:

Test set degamma shall be linear

Test set brightness and contrast shall be set to nominal

The diagonal size of the projected image shall be a minimum of 20 inches

The projections screen shall be 1X gain

The projected image shall be inspected from a 38 inch minimum viewing distance

The image shall be in focus during all image quality tests

- (11) Bright pixel definition: A single pixel or mirror that is stuck in the ON position and is visibly brighter than the surrounding pixels
- (12) Gray 10 screen definition: All areas of the screen are colored with the following settings:

Red = 10/255

Green = 10/255

Blue = 10/255

- (13) POM definition: Rectangular border of off-state mirrors surrounding the active area
- (14) Dark pixel definition: A single pixel or mirror that is stuck in the OFF position and is visibly darker than the surrounding pixels
- (15) Adjacent pixel definition: Two or more stuck pixels sharing a common border or common point, also referred to as a cluster
- (16) Unstable pixel definition: A single pixel or mirror that does not operate in sequence with parameters loaded into memory. The unstable pixel appears to be flickering asynchronously with the image

English Data Sheet: DLPS114



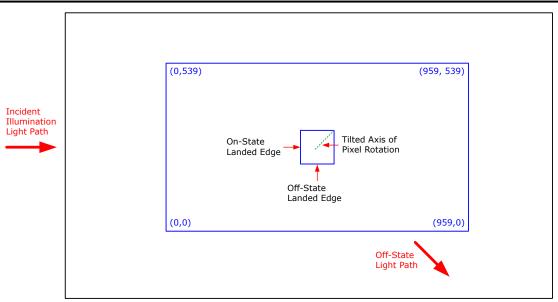


图 6-17. Landed Pixel Orientation and Tilt



#### **6.12 Window Characteristics**

PARAMETER <sup>(1)</sup> Window material designation			NOM	MAX	UNIT
			Corning Eagle XG		
Window refractive index At wavelength 546.1 nm			1.5119		
Window aperture				See (1)	
Illumination overfill				See (1)	
Window transmittance, single-pass	Minimum within the wavelength range 420 to 680 nm. Applies to all angles 0° to 30° AOI.	97%			
through both surfaces and glass	Average over the wavelength range 420 to 680 nm. Applies to all angles 30° to 45° AOI.	97%			

(1) See # 7.5 for more information.

# 6.13 Chipset Component Usage Specification

#### 备注

TI assumes no responsibility for image quality artifacts or DMD failures caused by optical system operating conditions exceeding limits described previously.

The is a component of one or more DLP chipsets. Reliable function and operation of the requires that it be used in conjunction with the other components of the applicable DLP chipset, including those components that contain or implement TI DMD control technology. TI DMD control technology consists of the TI technology and devices used for operating or controlling a DLP DMD.



# 7 Detailed Description

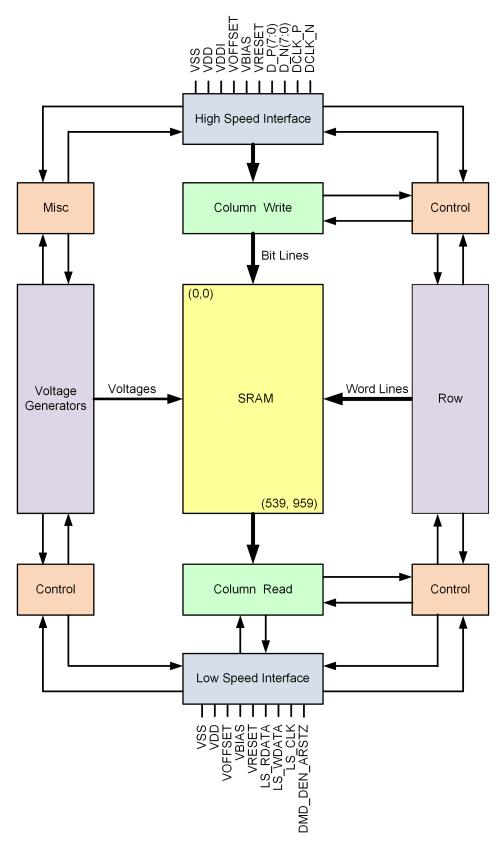
# 7.1 Overview

The DLP230GP is a 0.23-inch diagonal spatial light modulator of aluminum micromirrors. Pixel array size is 960 columns by 540 rows in a square grid pixel arrangement. The electrical interface is sub low voltage differential signaling (SubLVDS) data.

The DLP230GP is part of the chipset comprised of the DLP230GP DMD, the DLPC3432ZVB display controller, and the DLPA2000/2005/3000 PMIC/LED driver. To ensure reliable operation, the DLP230GP DMD must always be used with the DLPC3432ZVB display controller and the DLPA2000/2005/3000 PMIC/LED drivers.



# 7.2 Functional Block Diagram



A. Details omitted for clarity.



### 7.3 Feature Description

#### 7.3.1 Power Interface

The power management IC DLPA2000/2005/3000 contains three regulated DC supplies for the DMD reset circuitry:  $V_{BIAS}$ ,  $V_{RESET}$  and  $V_{OFFSET}$ , as well as the two regulated DC supplies for the DLPC3432ZVB controller.

### 7.3.2 Low-Speed Interface

The low speed interface handles instructions that configure the DMD and control reset operation. LS\_CLK is the low-speed clock, and LS\_WDATA is the low speed data input.

#### 7.3.3 High-Speed Interface

The purpose of the high-speed interface is to transfer pixel data rapidly and efficiently, making use of high speed DDR transfer and compression techniques to save power and time. The high-speed interface is composed of differential SubLVDS receivers for inputs with a dedicated clock.

#### **7.3.4 Timing**

The data sheet provides timing at the device pin. For output timing analysis, the tester pin electronics and its transmission line effects must be taken into account. 

6-13 shows an equivalent test load circuit for the output under test. Timing reference loads are not intended as a precise representation of any particular system environment or depiction of the actual load presented by a production test. System designers should use IBIS or other simulation tools to correlate the timing reference load to a system environment. The load capacitance value stated is only for characterization and measurement of AC timing signals. This load capacitance value does not indicate the maximum load the device is capable of driving.

#### 7.4 Device Functional Modes

DMD functional modes are controlled by the DLPC3432ZVB controller. See the DLPC3432ZVB controller data sheet or contact a TI applications engineer.

### 7.5 Optical Interface and System Image Quality Considerations

TI assumes no responsibility for end-equipment optical performance. Achieving the desired end-equipment optical performance involves making trade-offs between numerous component and system design parameters. Optimizing system optical performance and image quality strongly relate to optical system design parameter trades. Although it is not possible to anticipate every conceivable application, projector image quality and optical performance is contingent on compliance to the optical system operating conditions described in the following sections.

#### 7.5.1 Numerical Aperture and Stray Light Control

The angle defined by the numerical aperture of the illumination and projection optics at the DMD optical area should be the same. This angle should not exceed the nominal device mirror tilt angle unless appropriate apertures are added in the illumination and/or projection pupils to block out flat-state and stray light from the projection lens. The mirror tilt angle defines DMD capability to separate the ON optical path from any other light path, including undesirable flat-state specular reflections from the DMD window, DMD border structures, or other system surfaces near the DMD such as prism or lens surfaces. If the numerical aperture exceeds the mirror tilt angle, or if the projection numerical aperture angle is more than two degrees larger than the illumination numerical aperture angle, objectionable artifacts in the display border and/or active area could occur.

# 7.5.2 Pupil Match

TI's optical and image quality specifications assume that the exit pupil of the illumination optics is nominally centered within 2° of the entrance pupil of the projection optics. Misalignment of pupils can create objectionable artifacts in the display border and/or active area, which may require additional system apertures to control, especially if the numerical aperture of the system exceeds the pixel tilt angle.

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#### 7.5.3 Illumination Overfill

The active area of the device is surrounded by an aperture on the inside DMD window surface that masks structures of the DMD chip assembly from normal view and is sized to anticipate several optical operating conditions. Overfill light illuminating the window aperture can create artifacts from the edge of the window aperture opening and other surface anomalies that may be visible on the screen. The illumination optical system should be designed to limit the total light flux incident anywhere on the window aperture from exceeding approximately 10% of the total light flux in the active array. Depending on the particular optical architecture, overfill light may have to be further reduced below the suggested 10% level in order to be acceptable.

# 7.6 Micromirror Array Temperature Calculation

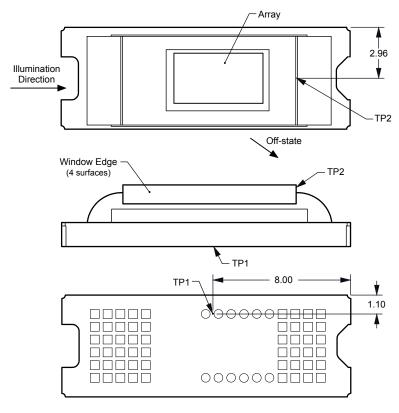


图 7-1. DMD Thermal Test Points

Micromirror array temperature cannot be measured directly, therefore it must be computed analytically from measurement points on the outside of the package, the package thermal resistance, the electrical power, and the illumination heat load. The relationship between array temperature and the reference ceramic temperature (thermal test point TP1 in 图 7-1) is provided by the following equations:

 $T_{ARRAY} = T_{CERAMIC} + (Q_{ARRAY} \times R_{ARRAY-TO-CERAMIC})$   $Q_{ARRAY} = Q_{ELECTRICAL} + Q_{ILLUMINATION}$ 

#### where

- T<sub>ARRAY</sub> = Computed array temperature (°C)
- T<sub>CFRAMIC</sub> = Measured ceramic temperature (°C) (TP1 location)
- R<sub>ARRAY-TO-CERAMIC</sub> = Thermal resistance of package specified in † 6.5 from array to ceramic TP1 (°C/Watt)



- Q<sub>ARRAY</sub> = Total DMD power on the array (W) (electrical + absorbed)
- Q<sub>ELECTRICAL</sub> = Nominal electrical power (W)
- Q<sub>INCIDENT</sub> = Incident illumination optical power (W)
- Q<sub>ILLUMINATION</sub> = (DMD average thermal absorptivity × Q<sub>INCIDENT</sub>) (W)
- DMD average thermal absorptivity = 0.4

The electrical power dissipation of the DMD is variable and depends on the voltages, data rates and operating frequencies. A nominal electrical power dissipation to use when calculating array temperature is 0.17 Watts. The absorbed power from the illumination source is variable and depends on the operating state of the micromirrors and the intensity of the light source. The equations shown above are valid for a single chip or multichip DMD system. It assumes an illumination distribution of 83.7% on the active array, and 16.3% on the array border.

The sample calculation for a typical projection application is as follows:

```
Q_{INCIDENT} = 2.9 W (measured)

T_{CERAMIC} = 55.0°C (measured)

Q_{ELECTRICAL} = 0.17 W

Q_{ARRAY} = 0.17 W + (0.40 × 2.9 W) =1.33 W

T_{ARRAY} = 55.0°C + (1.33 W × 9.0°C/W) = 67.0°C
```

# 7.7 Micromirror Power Density Calculation

The calculation of the optical power density of the illumination on the DMD in the different wavelength bands uses the total measured optical power on the DMD, percent illumination overfill, area of the active array, and ratio of the spectrum in the wavelength band of interest to the total spectral optical power.

- ILL<sub>UV</sub> = [OP<sub>UV-RATIO</sub> × Q<sub>INCIDENT</sub>] × 1000 ÷ A<sub>ILL</sub> (mW/cm<sup>2</sup>)
- ILL<sub>VIS</sub> = [OP<sub>VIS-RATIO</sub> × Q<sub>INCIDENT</sub>] ÷ A<sub>ILL</sub> (W/cm<sup>2</sup>)
- ILL<sub>IR</sub> =  $[OP_{IR-RATIO} \times Q_{INCIDENT}] \times 1000 \div A_{ILL} (mW/cm^2)$
- ILL<sub>BLU</sub> =  $[OP_{BLU-RATIO} \times Q_{INCIDENT}] \div A_{ILL} (W/cm^2)$
- ILL<sub>BLU1</sub> = [OP<sub>BLU1-RATIO</sub> × Q<sub>INCIDENT</sub>] ÷ A<sub>ILL</sub> (W/cm<sup>2</sup>)
- $A_{ILL} = A_{ARRAY} \div (1 OV_{ILL}) (cm^2)$

#### where:

- ILL<sub>UV</sub> = UV illumination power density on the DMD (mW/cm<sup>2</sup>)
- ILL<sub>VIS</sub> = VIS illumination power density on the DMD (W/cm<sup>2</sup>)
- ILL<sub>IR</sub> = IR illumination power density on the DMD (mW/cm<sup>2</sup>)
- ILL<sub>BLU</sub> = BLU illumination power density on the DMD (W/cm<sup>2</sup>)
- ILL<sub>BLU1</sub> = BLU1 illumination power density on the DMD (W/cm<sup>2</sup>)
- A<sub>ILL</sub> = illumination area on the DMD (cm<sup>2</sup>)
- Q<sub>INCIDENT</sub> = total incident optical power on DMD (W) (measured)
- A<sub>ARRAY</sub> = area of the array (cm<sup>2</sup>) (data sheet)
- OV<sub>ILL</sub> = percent of total illumination on the DMD outside the array (%) (optical model)

- OP<sub>UV-RATIO</sub> = ratio of the optical power for wavelengths <410 nm to the total optical power in the illumination spectrum (spectral measurement)
- OP<sub>VIS-RATIO</sub> = ratio of the optical power for wavelengths ≥410 and ≤800 nm to the total optical power in the illumination spectrum (spectral measurement)
- OP<sub>IR-RATIO</sub> = ratio of the optical power for wavelengths >800 nm to the total optical power in the illumination spectrum (spectral measurement)
- OP<sub>BLU-RATIO</sub> = ratio of the optical power for wavelengths ≥410 and ≤475 nm to the total optical power in the illumination spectrum (spectral measurement)
- OP<sub>BLU1-RATIO</sub> = ratio of the optical power for wavelengths ≥410 and ≤445 nm to the total optical power in the illumination spectrum (spectral measurement)

The illumination area varies and depends on the illumination overfill. The total illumination area on the DMD is the array area and overfill area around the array. The optical model is used to determine the percent of the total illumination on the DMD that is outside the array  $(OV_{ILL})$  and the percent of the total illumination that is on the active array. From these values the illumination area  $(A_{ILL})$  is calculated. The illumination is assumed to be uniform across the entire array.

From the measured illumination spectrum, the ratio of the optical power in the wavelength bands of interest to the total optical power is calculated.

#### Sample calculation:

```
\begin{aligned} &Q_{\text{INCIDENT}} = 2.90 \text{ W (measured)} \\ &A_{\text{ARRAY}} = (0.5184 \times 0.2916) = 0.1512 \text{ cm}^2 \text{ (data sheet)} \\ &OV_{\text{ILL}} = 16.3\% \text{ (optical model)} \\ &OP_{\text{UV-RATIO}} = 0.00021 \text{ (spectral measurement)} \\ &OP_{\text{VIS-RATIO}} = 0.99977 \text{ (spectral measurement)} \\ &OP_{\text{IR-RATIO}} = 0.00002 \text{ (spectral measurement)} \\ &OP_{\text{BLU-RATIO}} = 0.28100 \text{ (spectral measurement)} \\ &OP_{\text{BLU-RATIO}} = 0.03200 \text{ (spectral measurement)} \\ &A_{\text{ILL}} = 0.1512 \div (1 - 0.163) = 0.1806 \text{ cm}^2 \\ &ILL_{\text{UV}} = [0.00021 \times 2.90\text{W}] \times 1000 \div 0.1806 \text{ cm}^2 = 3.372 \text{ mW/cm}^2 \\ &ILL_{\text{VIS}} = [0.99977 \times 2.90\text{W}] \div 0.1806 \text{ cm}^2 = 16.05 \text{ W/cm}^2 \\ &ILL_{\text{IR}} = [0.00002 \times 2.90\text{W}] \times 1000 \div 0.1806 \text{ cm}^2 = 0.321 \text{ mW/cm}^2 \\ &ILL_{\text{BLU}} = [0.28100 \times 2.90\text{W}] \div 0.1806 \text{ cm}^2 = 4.51 \text{ W/cm}^2 \\ &ILL_{\text{BLU}} = [0.03200 \times 2.90\text{W}] \div 0.1806 \text{ cm}^2 = 0.51 \text{ W/cm}^2 \end{aligned}
```

#### 7.8 Micromirror Landed-On/Landed-Off Duty Cycle

#### 7.8.1 Definition of Micromirror Landed-On/Landed-Off Duty Cycle

The micromirror landed-on/landed-off duty cycle (landed duty cycle) denotes the amount of time (as a percentage) that an individual micromirror is landed in the ON state versus the amount of time the same micromirror is landed in the OFF state.



As an example, a landed duty cycle of 100/0100/0 indicates that the referenced pixel is in the ON state 100%100% of the time (and in the OFF state 0%0% of the time), whereas 0/1000/100 would indicate that the pixel is in the OFF state 100% 100% of the time. Likewise, 50/50 indicates that the pixel is ON 50% of the time and OFF 50% of the time.

Note that when assessing landed duty cycle, the time spent switching from one state (ON or OFF) to the other state (OFF or ON) is considered negligible and is thus ignored.

Since a micromirror can only be landed in one state or the other (ON or OFF), the two numbers (percentages) always add to 100.

### 7.8.2 Landed Duty Cycle and Useful Life of the DMD

Knowing the long-term average landed duty cycle (of the end product or application) is important because subjecting all (or a portion) of the DMD micromirror array (also called the active array) to an asymmetric landed duty cycle for a prolonged period of time can reduce the usable life of the DMD.

Note that it is the symmetry/asymmetry of the landed duty cycle that is of relevance. The symmetry of the landed duty cycle is determined by how close the two numbers (percentages) are to being equal. For example, a landed duty cycle of 50/50 is perfectly symmetrical whereas a landed duty cycle of 100/0 or 0/100 is perfectly asymmetrical.

Product Folder Links: DLP230GP

# 7.8.3 Landed Duty Cycle and Operational DMD Temperature

Operational DMD temperature and landed duty cycle interact to affect the usable life of the DMD, and this interaction can be exploited to reduce the impact that an asymmetrical landed duty cycle has on the usable life of the DMD. The relationship between temperature and landed duty cycle is quantified in the de-rating curve shown in 图 6-1. The importance of this curve is that:

- All points along this curve represent the same usable life.
- All points above this curve represent lower usable life (and the further away from the curve, the lower the usable life).
- All points below this curve represent higher usable life (and the further away from the curve, the higher the usable life).

In practice, this curve specifies the maximum operating DMD temperature that the DMD should be operated at for a given long-term average landed duty cycle.

#### 7.8.4 Estimating the Long-Term Average Landed Duty Cycle of a Product or Application

During a given period of time, the landed duty cycle of a given pixel follows from the image content being displayed by that pixel.

For example, in the simplest case, when displaying pure-white on a given pixel for a given time period, that pixel will experience close to a 100/0 landed duty cycle during that time period. Likewise, when displaying pure-black, the pixel will experience close to a 0/100 landed duty cycle.

Between the two extremes (ignoring for the moment color and any image processing that may be applied to an incoming image), the landed duty cycle tracks one-to-one with the gray scale value, as shown in 表 7-1.

表 7-1. Grayscale Value and Nominal Landed Duty Cvcle

	,
Grayscale Value	Landed Duty Cycle
0%	0/100
10%	10/90
20%	20/80
30%	30/70
40%	40/60
50%	50/50
60%	60/40
70%	70/30
80%	80/20
90%	90/10
100%	100/0

Accounting for color rendition (but still ignoring image processing) requires knowing both the color intensity (from 0% to 100%) for each constituent primary color (red, green, and/or blue) for the given pixel as well as the color cycle time for each primary color, where "color cycle time" is the total percentage of the frame time that a given primary must be displayed in order to achieve the desired white point.

During a given period of time, the landed duty cycle of a given pixel can be calculated as follows:

where



Red\_Cycle\_%, Green\_Cycle\_%, and Blue\_Cycle\_% represent the percentage of the frame time that red, green, and blue are displayed (respectively) to achieve the desired white point.

For example, assuming that the red, green and blue color cycle times are 50%, 20%, and 30% respectively (in order to achieve the desired white point), then the landed duty cycle for various combinations of red, green, blue color intensities would be as shown in  $\frac{1}{2}$  7-2.

表 7-2. Example Nominal Landed Duty Cycle for Full-Color Pixels

Red Cycle	Green Cycle	Blue Cycle
Percentage	Percentage	Percentage
50%	20%	30%

Red Scale Value	Green Scale Value	Blue Scale Value	Landed Duty Cycle
0%	0%	0%	0/100
100%	0%	0%	50/50
0%	100%	0%	20/80
0%	0%	100%	30/70
12%	0%	0%	6/94
0%	35%	0%	7/93
0%	0%	60%	18/82
100%	100%	0%	70/30
0%	100%	100%	50/50
100%	0%	100%	80/20
12%	35%	0%	13/87
0%	35%	60%	25/75
12%	0%	60%	24/76
100%	100%	100%	100/0

The last factor to account for in estimating the landed duty cycle is any applied image processing. Within the DLP controller DLPC3432ZVB, the two functions which affect the landed duty cycle are gamma and IntelliBright™.

Gamma is a power function of the form  $Output\_Level = A \times Input\_Level^{Gamma}$ , where A is a scaling factor that is typically set to 1.

In the DLPC3432ZVB controller, gamma is applied to the incoming image data on a pixel-by-pixel basis. A typical gamma factor is 2.2, which transforms the incoming data as shown in ₹ 7-2.

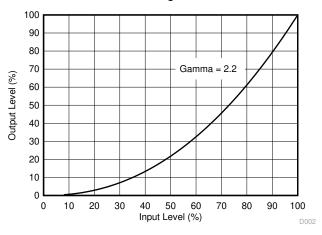


图 7-2. Example of Gamma = 2.2



From \$\mathbb{Z}\$ 7-2, if the gray scale value of a given input pixel is 40% (before gamma is applied), then gray scale value will be 13% after gamma is applied. Therefore, it can be seen that since gamma has a direct impact displayed gray scale level of a pixel, it also has a direct impact on the landed duty cycle of a pixel.

The content adaptive illumination control (CAIC) and local area brightness boost (LABB) of the IntelliBright algorithm also apply transform functions on the gray scale level of each pixel.

But while the amount of gamma applied to every pixel of every frame is constant (the exponent, gamma, is constant), CAIC and LABB are both adaptive functions that can apply different amounts of either boost or compression to every pixel of every frame.

Consideration must also be given to any image processing which occurs before the DLPC3432ZVB controller.



# 8 Application and Implementation

#### 备注

以下应用部分中的信息不属于 TI 器件规格的范围,TI 不担保其准确性和完整性。TI 的客 户应负责确定器件是否适用于其应用。客户应验证并测试其设计,以确保系统功能。

### 8.1 Application Information

The DMDs are spatial light modulators which reflect incoming light from an illumination source to one of two directions, with the primary direction being into a projection or collection optic. Each application is derived primarily from the optical architecture of the system and the format of the data coming into the DLPC3432/3472 controller. The new high tilt pixel in the side-illuminated DMD increases brightness performance and enables a smaller system footprint for thickness-constrained applications. Applications of interest include projection technology embedded in display devices like ultra low-power battery operated mobile accessory projectors, phones, tablets, ultra-mobile low-end Smart TVs, and virtual assistants.

DMD power-up and power-down sequencing is strictly controlled by the DLPA2000/2005/3000 . Refer to # 9 for power-up and power-down specifications. To ensure reliable operation, the DLP230GP DMD must always be used with the DLPC3432/3472 display controller and a DLPA2000/2005/3000 PMIC/LED driver.

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### 8.2 Typical Application

A common application when using a DLP230GP DMD and a DLPC3432/3472 is for creating a pico projector that can be used as an accessory to a smartphone, tablet, or a laptop. The DLPC3432/3472 in the pico projector receives images from a multimedia front end within the product as shown in 88-1.

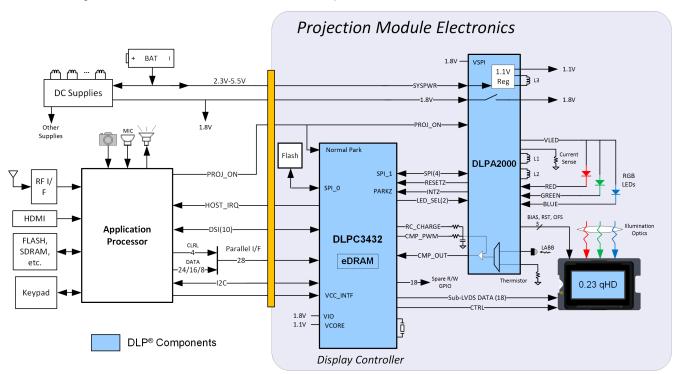


图 8-1. Typical Application Diagram

### 8.2.1 Design Requirements

A pico projector is created by using a DLP chipset comprised of a DLP230GP DMD, a DLPC3432/3472 controller, and a DLPA2000/2005/3000 PMIC/LED driver. The DLPC3432/3472 controller performs the digital image processing, the DLPA2000/2005/3000 provides the needed analog functions for the projector, and the DLP230GP DMD is the display device for producing the projected image.

In addition to the three DLP chips in the chipset, other chips are needed. At a minimum a flash part is needed to store the DLPC3432/3472 controller software.

The illumination light that is applied to the DMD is typically from red, green, and blue LEDs. These are often contained in three separate packages, but sometimes more than one color of LED die may be in the same package to reduce the overall size of the pico projector.

The DLPC3432/3472 controller receives image data from the multimedia front end over a 24-bit parallel interface. An I<sup>2</sup>C interface should be connected from the multimedia front end for sending commands to the DLPC3432/3472 controller for configuring the chipset for different features.

#### 8.2.2 Detailed Design Procedure

For instructions on how to connect the DLPC3432/3472 controller, the DLPA2000/2005/3000 , and the DLP230GP DMD together, see the reference design schematic. When a circuit board layout is created from this schematic a very small circuit board is possible. An example small board layout is included in the reference design data base. Layout guidelines should be followed to achieve a reliable projector.

The optical engine that has the LED packages and the DMD mounted to it is typically supplied by an optical OEM who specializes in designing optics for DLP projectors.



### 8.2.3 Application Curve

As the LED currents that are driven time-sequentially through the red, green, and blue LEDs are increased, the brightness of the projector increases. This increase is somewhat non-linear, and the curve for typical white screen lumens changes with LED currents is as shown in 88-2. For the LED currents shown, it is assumed that the same current amplitude is applied to the red, green, and blue LEDs.

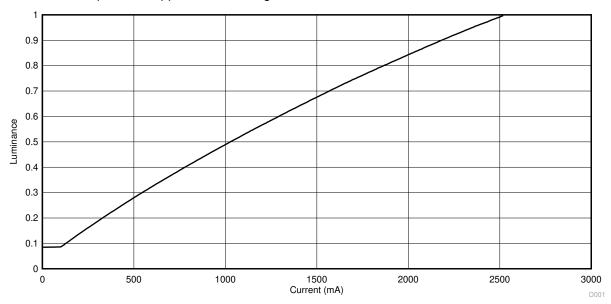


图 8-2. Luminance vs Current



# 9 Power Supply Recommendations

The following power supplies are all required to operate the DMD:  $V_{DD}$ ,  $V_{DDI}$ ,  $V_{OFFSET}$ ,  $V_{BIAS}$ , and  $V_{RESET}$ . All  $V_{SS}$  connections are also required. DMD power-up and power-down sequencing is strictly controlled by the DLPA2000/2005/3000 devices.

#### **CAUTION**

For reliable operation of the DMD, the following power supply sequencing requirements must be followed. Failure to adhere to the prescribed power-up and power-down procedures may affect device reliability.

# 9.1 Power Supply Power-Up Procedure

- During power-up, V<sub>DD</sub> and V<sub>DDI</sub> must always start and settle before V<sub>OFFSET</sub>, V<sub>BIAS</sub>, and V<sub>RESET</sub> voltages are applied to the DMD.
- During power-up, it is a strict requirement that the delta between V<sub>BIAS</sub> and V<sub>OFFSET</sub> must be within the specified limit shown in #6.4. Refer to ₹9-2 for power-up delay requirements.
- During power-up, the LPSDR input pins of the DMD shall not be driven high until after V<sub>DD</sub> and V<sub>DDI</sub> have settled at operating voltage.
- During power-up, there is no requirement for the relative timing of V<sub>RESET</sub> with respect to V<sub>OFFSET</sub> and V<sub>BIAS</sub>. Power supply slew rates during power-up are flexible, provided that the transient voltage levels follow the requirements listed previously and in 

  9-1.

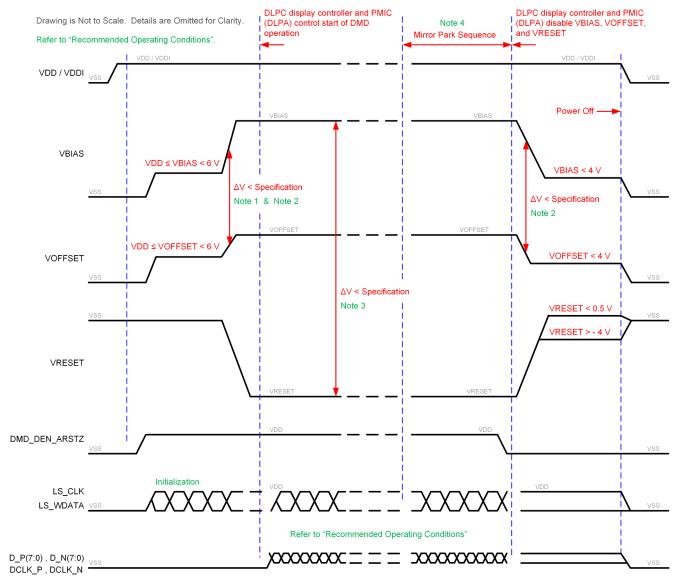
# 9.2 Power Supply Power-Down Procedure

- The power-down sequence is the reverse order of the previous power-up sequence. V<sub>DD</sub> and V<sub>DDI</sub> must be supplied until after V<sub>BIAS</sub>, V<sub>RESET</sub>, and V<sub>OFFSET</sub> are discharged to within 4 V of ground.
- During power-down, it is not mandatory to stop driving V<sub>BIAS</sub> prior to V<sub>OFFSET</sub>, but it is a strict requirement that
  the delta between V<sub>BIAS</sub> and V<sub>OFFSET</sub> must be within the specified limit shown in # 6.4 (Refer to Note 2 for 
  9-1).
- During power-down, the LPSDR input pins of the DMD must be less than V<sub>DDI</sub>, the specified limit shown in #6.4.
- During power-down, there is no requirement for the relative timing of V<sub>RESET</sub> with respect to V<sub>OFFSET</sub> and V<sub>BIAS</sub>.
- Power supply slew rates during power-down are flexible, provided that the transient voltage levels follow the requirements listed previously and in 

  9-1.



### 9.3 Power Supply Sequencing Requirements



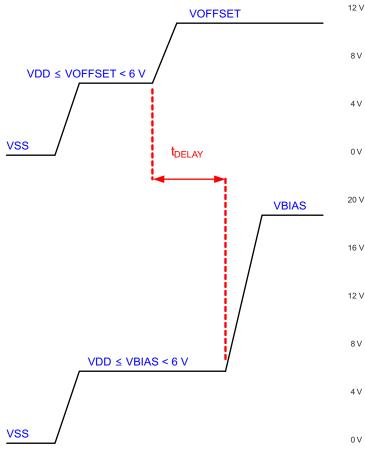
- A. Refer to 表 9-1 and 图 9-2 for critical power-up sequence delay requirements.
- B. To prevent excess current, the supply voltage delta |V<sub>BIAS</sub> V<sub>OFFSET</sub>| must be less than specified in #6.4. OEMs may find that the most reliable way to ensure this is to power V<sub>OFFSET</sub> prior to V<sub>BIAS</sub> during power-up and to remove V<sub>BIAS</sub> prior to V<sub>OFFSET</sub> during power-down. Refer to 表 9-1 and 图 9-2 for power-up delay requirements.
- C. To prevent excess current, the supply voltage delta  $|V_{BIAS} V_{RESET}|$  must be less than the specified limit shown in #6.4.
- D. When system power is interrupted, the DLPA2000/2005/3000 initiates hardware power-down that disables V<sub>BIAS</sub>, V<sub>RESET</sub> and V<sub>OFFSET</sub> after the micromirror park sequence.
- E. Drawing is not to scale and details are omitted for clarity.

#### 图 9-1. Power Supply Sequencing Requirements (Power Up and Power Down)



表 9-1. Power-Up Sequence Delay Requirement

	PARAMETER	MIN	MAX	UNIT
t <sub>DELAY</sub>	Delay requirement from V <sub>OFFSET</sub> power up to V <sub>BIAS</sub> power up	2		ms
V <sub>OFFSET</sub>	Supply voltage level at beginning of power–up sequence delay (see 图 9-2)		6	V
V <sub>BIAS</sub>	Supply voltage level at end of power–up sequence delay (see 图 9-2)		6	V



Refer to  $\frac{1}{8}$  9-1 for  $V_{\text{OFFSET}}$  and  $V_{\text{BIAS}}$  supply voltage levels during power-up sequence delay.

图 9-2. Power-Up Sequence Delay Requirement



# 10 Layout

# 10.1 Layout Guidelines

The DLP230GP DMD is connected to a PCB or a flex circuit using an interposer. For additional layout guidelines regarding length matching, impedance, etc. see the DLPC3432 and DLPC3472 controller datasheet. For a detailed layout example refer to the layout design files. Some layout guidelines for routing to the DLP230GP DMD are:

- Match lengths for the LS\_WDATA and LS\_CLK signals.
- Minimize vias, layer changes, and turns for the HS bus signals. Refer to 图 10-1.
- Minimum of two 100-nF (25 V) capacitors one close to V<sub>BIAS</sub> pin. Capacitors C4 and C8 in 图 10-1.
- Minimum of two 100-nF (25 V) capacitors one close to each V<sub>RST</sub> pin. Capacitors C3 and C7 in 图 10-1.
- Minimum of two 220-nF (25 V) capacitors one close to each V<sub>OFS</sub> pin. Capacitors C5 and C6 in 图 10-1.
- Minimum of four 100-nF (6.3 V) capacitors two close to each side of the DMD. Capacitors C1, C2, C9 and C10 in 图 10-1.

# 10.2 Layout Example

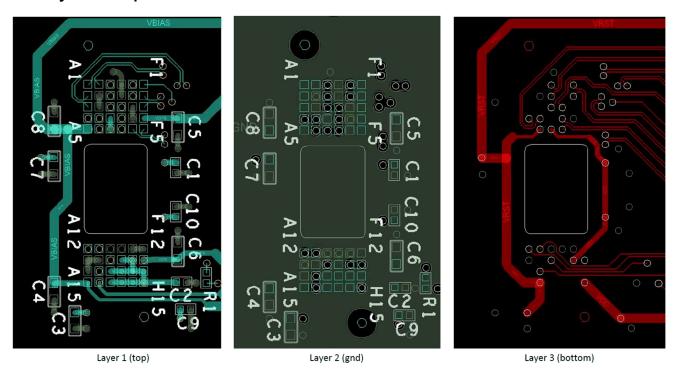


图 10-1. Power Supply Connections



# 11 Device and Documentation Support

# 11.1 Device Support

#### 11.1.1 第三方产品免责声明

TI 发布的与第三方产品或服务有关的信息,不能构成与此类产品或服务或保修的适用性有关的认可,不能构成此类产品或服务单独或与任何 TI 产品或服务一起的表示或认可。

#### 11.1.2 Device Nomenclature

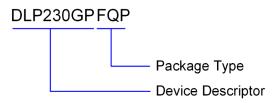


图 11-1. Part Number Description

### 11.1.3 Device Markings

The device marking includes the legible character string GHJJJJK DLP230GPFQP. GHJJJJK is the lot trace code. DLP230GPFQP is the abbreviated part number.

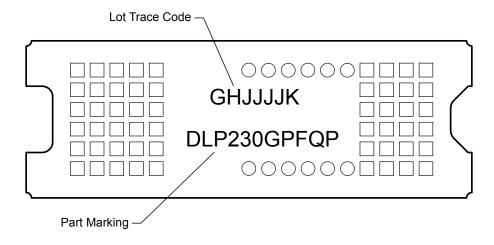


图 11-2. DMD Marking

#### 11.2 接收文档更新通知

要接收文档更新通知,请导航至 ti.com 上的器件产品文件夹。点击*订阅更新* 进行注册,即可每周接收产品信息更 改摘要。有关更改的详细信息,请查看任何已修订文档中包含的修订历史记录。

#### 11.3 支持资源

TI E2E<sup>™</sup> 支持论坛是工程师的重要参考资料,可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解 答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者"按原样"提供。这些内容并不构成 TI 技术规范,并且不一定反映 TI 的观点;请参阅 TI 的《使用条款》。

#### 11.4 Trademarks

IntelliBright<sup>™</sup> is a trademark of Texas Instruments.

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

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### 11.5 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序,可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级,大至整个器件故障。精密的集成电路可能更容易受到损坏,这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

#### 11.6 术语表

TI术语表

本术语表列出并解释了术语、首字母缩略词和定义。

# 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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English Data Sheet: DLPS114

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#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
	( )	( )			(-)	(4)	(5)		(-/
DLP230GPAFQP	Active	Production	CLGA (FQP)   54	140   JEDEC TRAY (5+1)	Yes	NIAU	N/A for Pkg Type	0 to 70	
DLP230GPAFQP.A	Active	Production	CLGA (FQP)   54	140   JEDEC TRAY (5+1)	Yes	NIAU	N/A for Pkg Type	0 to 70	
DLP230GPAFQP.B	Active	Production	CLGA (FQP)   54	140   JEDEC TRAY (5+1)	Yes	NIAU	N/A for Pkg Type	0 to 70	

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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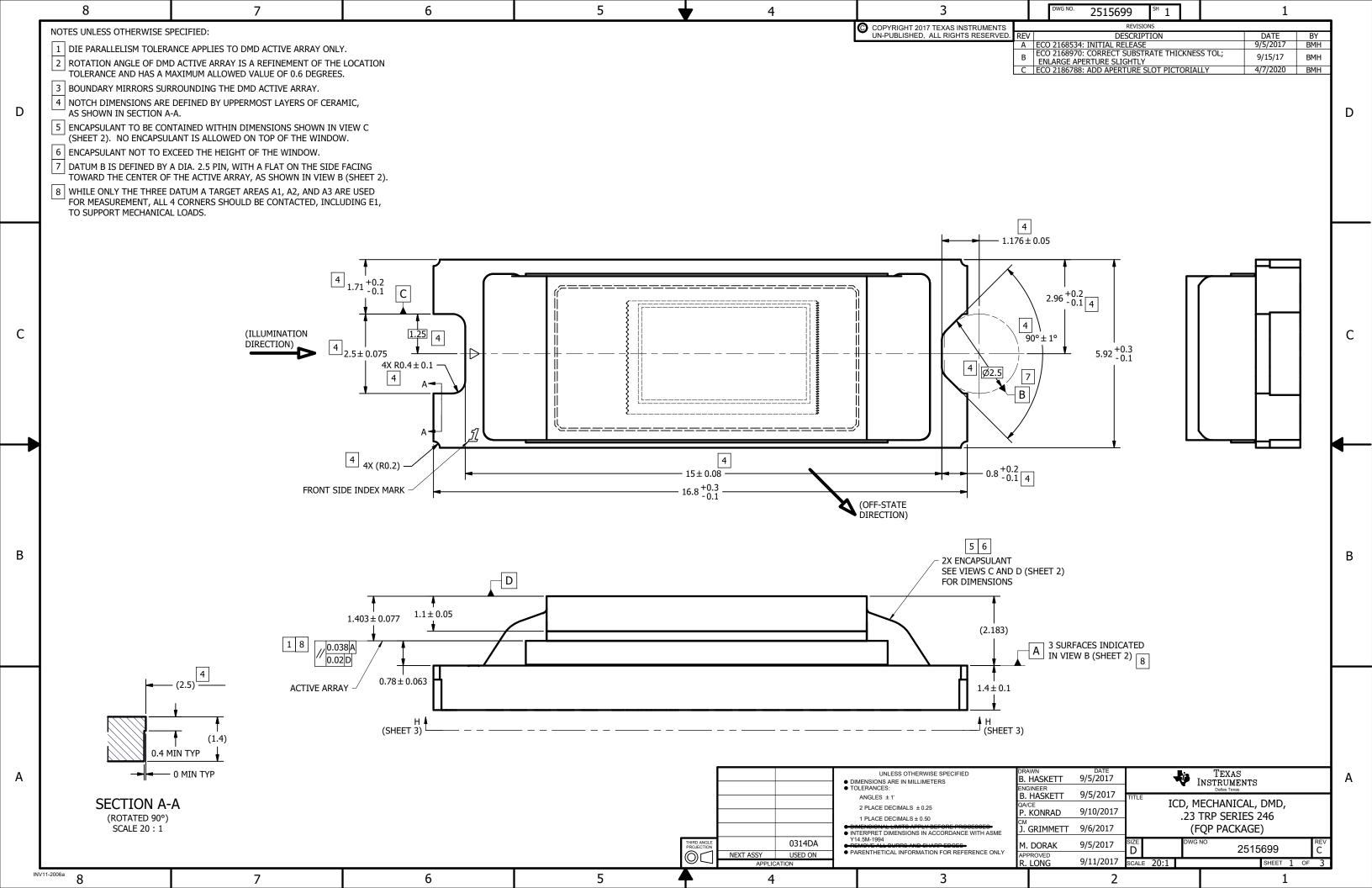
<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

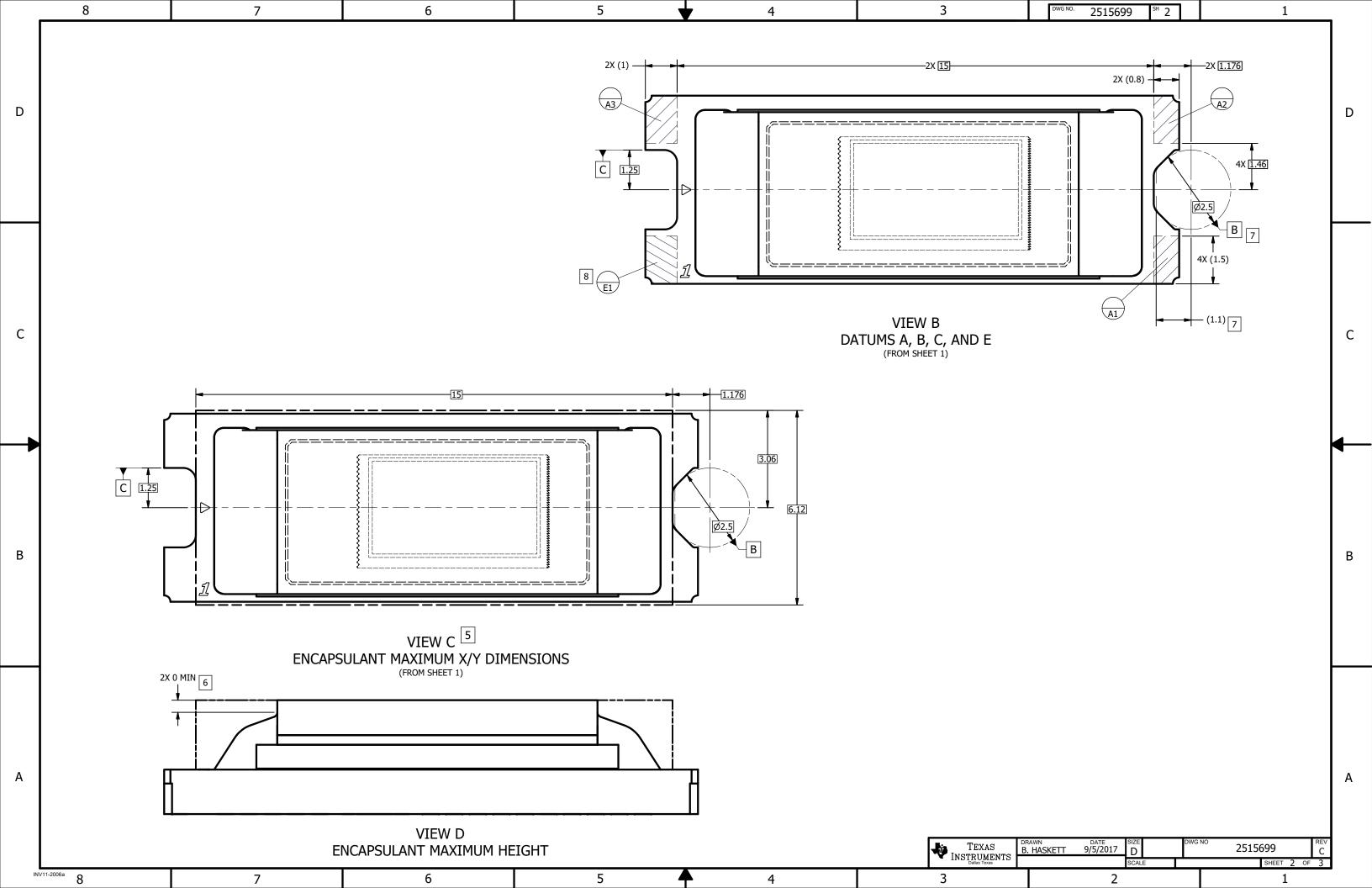
<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

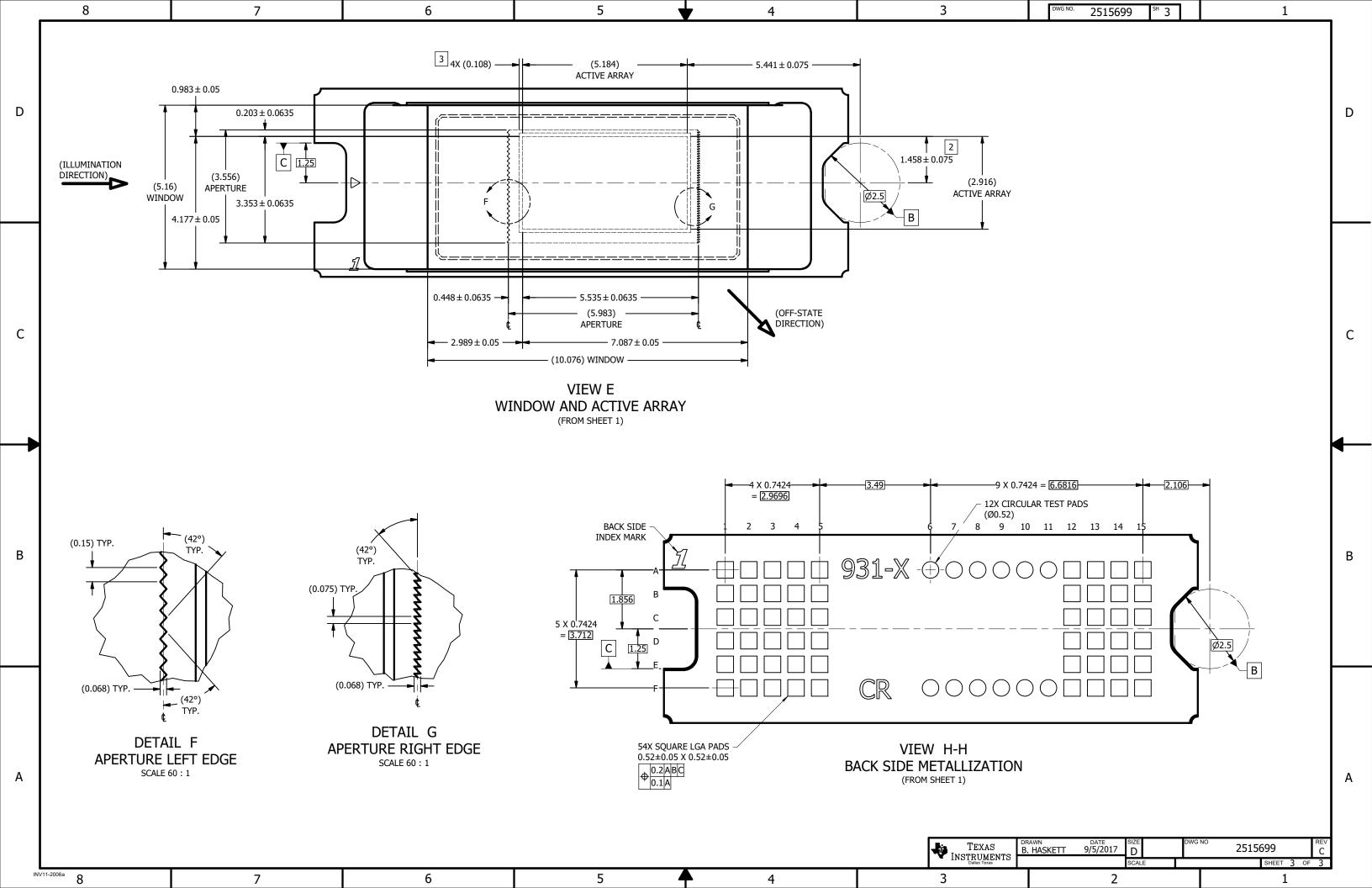
<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.







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